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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/586,176	04/06/2007	Ross Alan Kohler	Kohler 10-31-39	2823	
	7590 03/23/200 ON & LEWIS, LLP	EXAMINER			
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SUITE 205 FAIRFIELD, C	CT 06824		ART UNIT	PAPER NUMBER	
		2827			
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			03/23/2009	PAPER	

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Advisory Action Before the Filing of an Appeal Brief

Application No.	Applicant(s)		
10/586,176	KOHLER ET AL.		
Examiner	Art Unit		
FERNANDO N. HIDALGO	2827		

		TETATORIES IN THE TEST	2021					
	-The MAILING DATE of this communication appe	ars on the cover sheet with the o	correspondence add	ress				
THE REPL	Y FILED 27 February 2009 FAILS TO PLACE THIS	APPLICATION IN CONDITION FO	R ALLOWANCE.					
appli appli for C	ne reply was filed after a final rejection, but prior to or on the same day as filing a Notice of Appeal. To avoid abandonment of this optication, applicant must timely file one of the following replies: (1) an amendment, affidavit, or other evidence, which places the pplication in condition for allowance; (2) a Notice of Appeal (with appeal fee) in compliance with 37 CFR 4.131; or (3) a Request or Continued Examination (RCE) in compliance with 37 CFR 1.114. The reply must be filed within one of the following time priods:							
	The period for reply expiresmonths from the mailing							
· — n	no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of the final rejection.							
N.	Examiner Note: If box 1 is checked, check either box (a) or (MONTHS OF THE FINAL REJECTION. See MPEP 706.07(f).						
Extensions of time may be obtained under 37 CFR 1.136(a). The date on which the petition under 37 CFR 1.136(a) and the appropriate extension fee have been filled is the date for purposes of determining the period of extension and the corresponding amount of the fee. The appropriate extension fee under 37 CFR 1.17(a) is calculated from: (1) the expiration date of the shortened statutory period for reply originally set in the final Office action; or (2) as set forth in (b) above, if checked. Any reply received by the Office later than three months after the mailting date of the final rejection, even if timely filled, may reduce any earmed pattent term adjustment. See 37 CFR 1.704(b).								
	FAPPEAL							
2. The Notice of Appeal was filed on A brief in compliance with 37 CFR 41.37 must be filed within two months of the date filing the Notice of Appeal (37 CFR 41.37(a)), or any extension thereof (37 CFR 41.37(e)), to avoid dismissal of the appeal. Sin Notice of Appeal has been filed, any reply must be filed within the time period set forth in 37 CFR 41.37(a). AMENDMENTS								
		out prior to the date of filing a brief	will not be entered be	couse				
 \(\)\(\) The proposed amendment(s) flide after a final rejection, but prior to the date of filing a brief, will not be entered because \(\)\(\)\(\) They raise new issues that would require further consideration and/or search (see NOTE below); \(\)\(\)\(\)\(\)\(\)\(\)\(\)\(\								
(c) 🗵	They are not deemed to place the application in bet appeal; and/or	ter form for appeal by materially rec	ducing or simplifying t	ne issues for				
(d)	They present additional claims without canceling a	corresponding number of finally reje	ected claims.					
. — -	NOTE: (See 37 CFR 1.116 and 41.33(a)).	A Government of Mark of Albert Co.	areas a seed seed to	DTO! 004)				
=	amendments are not in compliance with 37 CFR 1.12		mpliant Amendment (I	PTOL-324).				
	licant's reply has overcome the following rejection(s): //y proposed or amended claim(s) would be all							
non-a	allowable claim(s).		•					
how	ourposes of appeal, the proposed amendment(s): a) the new or amended claims would be rejected is prov		I be entered and an e	xplanation of				
	status of the claim(s) is (or will be) as follows:							
	n(s) allowed: n(s) objected to:							
	n(s) rejected to: n(s) rejected: <u>1-31</u> .							
	n(s) withdrawn from consideration:							
AFFIDAVI	F OR OTHER EVIDENCE							
beca	affidavit or other evidence filed after a final action, bu use applicant failed to provide a showing of good and not earlier presented. See 37 CFR 1.116(e).							
enter	affidavit or other evidence filed after the date of filing red because the affidavit or other evidence failed to o ring a good and sufficient reasons why it is necessary	vercome all rejections under appea	al and/or appellant fail:	s to provide a				
10. The affidavit or other evidence is entered. An explanation of the status of the claims after entry is below or attached. REQUEST FOR RECONSIDERATION/OTHER								
11. The request for reconsideration has been considered but does NOT place the application in condition for allowance because: See Continuation Sheet.								

13. Other: ____.
/AMIR ZARABIAN/

Supervisory Patent Examiner, Art Unit 2827

12. Note the attached Information Disclosure Statement(s). (PTO/SB/08) Paper No(s).

Continuation of 11. does NOT place the application in condition for allowance because: the remarks filed on 2/27/09, in regard to independent claims 1, 11, 21, 24 and 27, submit that the teachings of Reiner do not disclose "programming using hot carrier." As well known in the art, and incidentally finding support in paragraph [0018] of the specifications of the instant application, hot carrier effects, normally caused over time in the routine use of a transistor, can be accelerated by the use of high voltage bissing thus causing channel degradation at a drain/source junction by the voltage bissing hereto. Page 4 of Reiner, furthermore, exemplarily teaches that high voltage levels result in degradation of the memory device due to an increased heating of the carrier (hot carrier effecs) in agreement, but anticipation the teachings found in paragraph 10018 of the instant application. Reiner further teaches on page "Hot carrier effects occur

It has thus to be ensured that no inclerable degradation of the memory circuit occurs ... That is, unquestionably and objectively clear that hot carrier effects occur and that intolerable degradation (memory rendered useless in plain language) occurance is to be avoided. Therefore, contrary to the submission in the remarks that Reiner teaches away "by teaching to avoid hot carrier conditions." Reiner, in fact, teaches programming, wherein hot carrier effects occur, but sensibly cautions that no INTOLERABLE DEGRADATION be permitted. degradation that would render the memory device useless, inoperable. The remarks further suggest that there was no reason to combine the prior art references used because there is no suggestion in Reiner of using hot carrier techniques. This conclusion is irrational in view of the clearly established teachings of hot carrier effects in OTP memory as taught at least by Reiner. Page 10 of the remarks submit that Reiner does not overcome the claim of a memory cell, comprising only one transistor of claim 24. Reiner, at least on page 5, teaches "a memory transistor T2." A select transistor, for selectively programming the one memory transistor, is available. This is no different from the instant application, wherein in at least the Abstract and paragraph [0006] it is disclosed that "transistors in the array are selectively programmed: "The present invention recognizes that such characteristics changes can be SELECTIVELY applied to memory cells in the OTP memory devices ... " That is both the OTP of Reiner and the OTP of the instant application have a one transistor memory selectively programmed by inherent means such as a select transistor. Inherently, there is absolutelly no way, technique, manner or method that would progam a one-transistor memory without means for first selecting it for applying voltage biasing conditions. In regard to the rejection of claim 27, the remarks submit, incomprehensibly, that the preamble of said claim, "An integrated circuit," is not taught by the prior art references. Reiner, in at least page 2, lines 4-8, and page 6, lines 20-21, teaches what is inherent in semiconductor circuit design in general and OTP memory in particular; programming means for applying voltages to the OTP memory and readout means (sense amplifier circuitry) for reading the OTP memory. Unquestionably, these means and the OTP memory are inherent parts of an integrated circuit. Any claims to the contrary are suspect at best. In regard to at least dependent claims 3, 13, 23 and 29, the remarks submit that Reiner does not teach "said altered characteristics." On the contrary, Reiner is amply clear, on page 7, that programmability of the memory cell can be determined by the anount of current passing through the memory channel; below a predetermined detection level is considered no programming, above said level is considered programming. Furthermore, it is well known in the art, unquestionably to one of ordinary skill in said art, that threhold voltage is in direct relationship to the current through a transistor channel. This is inherently so whether the transistor is in normal use (no prevalent hot carrier effects) or when bot carrier effects are involved. In regard to dependent claims 4 and 14, the remarks submit that Reiner does not teach programming appliting a stressful voltage to a drain and a gate. Reiner, contrary to this assertion, teaches in at least page 4 a high drain voltage and a moderate gate voltage in order to induce hot carrier effects, as such the drain and gate voltages are stressful enough. In reagard to dependent claims 5, 15 and 30, Reiner in at least page 6 teaches "A subsequent readout of the memory by readout means (sensing detection) of the current (thus threshold) of the memory. In regard to dependent claims 7, 17, 31, 8, 18, 9 and 19, it is believed sufficient analysis of the teachings of Reiner has been presented as set forth above. In regard to dependent claims 10 and 20, the remarks submit that Reiner does not teach or mention rows or raising the gate terminal. In any memory array, memory elements of cells are inherently organized in rows and columns. FIG. 5A is one example of a memory cell addressed by rows and columns and Reiner in at least page 2 teaches applying a gate voltage on the memory cell. These teachings contradict the submission on page 13 of the remarks. Finally, as set forth above, it is believed the instatn application, as claimed, is in no better condition for allowance.